



浩畅半导体
www.szhaochang.cn

BFS20 NPN Medium Frequency Transistor

SOT-23 Plastic-Encapsulate Transistors

产
品
规
格
书

承
认
书

客户确认：

公司签章：

部门	工程部	品保部	采购部
签名			
日期			

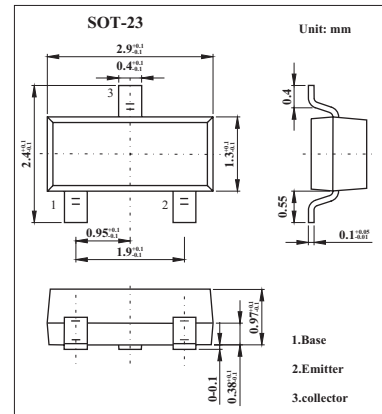


SOT-23 Plastic-Encapsulate Transistors

BFS20 NPN Medium Frequency Transistor

■ Features

- Low current (max. 25 mA)
- Low voltage (max. 20 V)
- Very low feedback capacitance (typ. 350 fF).



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CB0}	30	V
Collector-emitter voltage	V _{CE0}	20	V
Emitter-base voltage	V _{EB0}	4	V
Collector current	I _C	25	mA
Peak collector current	I _{CM}	25	mA
power dissipation	P _D	250	mW
Thermal resistance from junction to ambient *	R _{th j-a}	500	K/W
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-65 to +150	°C

* Transistor mounted on an FR4 printed-circuit board.

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector cutoff current	I _{CB0}	I _E = 0; V _{CB} = 20 V			100	nA
	I _{CB0}	I _E = 0; V _{CB} = 20 V; T _j = 100 °C			10	μ A
Emitter cutoff current	I _{EB0}	I _C = 0; V _{EB} = 4V			100	nA
DC current gain	h _{FE}	I _C = 7mA; V _{CE} = 10 V	40	85		
Base to emitter voltage	V _{BE}	I _C = 7 mA; V _{CE} = 10V		740	900	mV
Collector capacitance	C _C	I _E = i _e = 0; V _{CB} = 10 V; f = 1 MHz		1		pF
Freedback capacitance	C _{re}	I _C =0,V _{CB} =10V,f=1MHz		350		pF
Transition frequency	f _T	I _C =5mA; V _{CE} =10 V; f = 100 MHz	275	450		MHz

■ Marking

Marking	G1
---------	----